



MCR100-6U-8U Plastic-Encapsulate Thyristors

Silicon Controlled Rectifier



FEATURES

Current- I_{GT} : 200 μ A

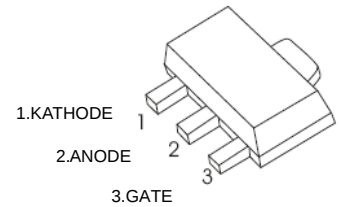
I_{TRMS} : 0.8 A

V_{RRM}/V_{DRM} : MCR100-6: 400 V

MCR100-8: 600 V

Operating and storage junction temperature range

T_J, T_{stg} : -55°C to +150°C



SOT-89-3L

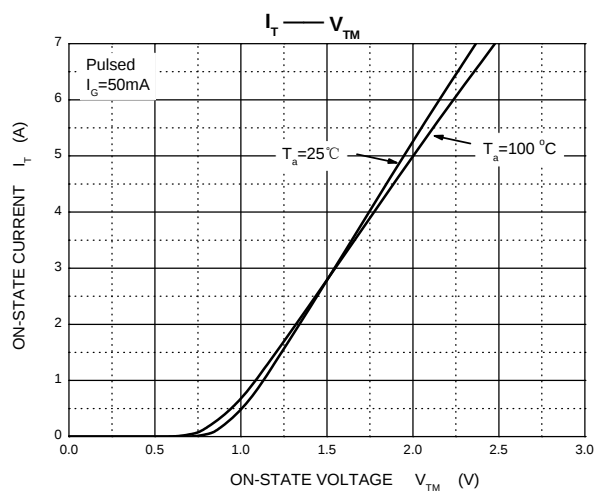
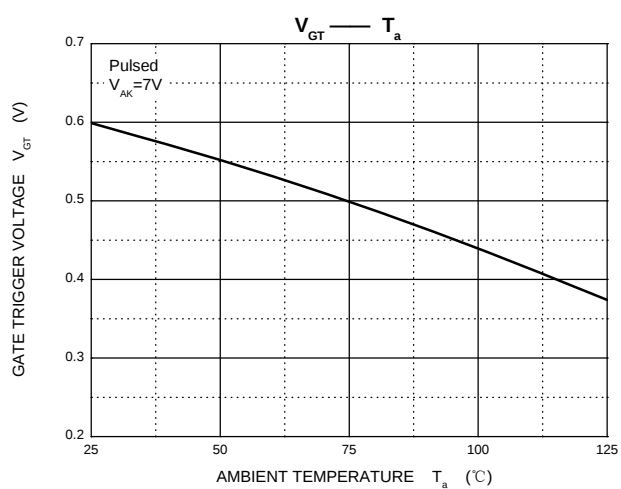
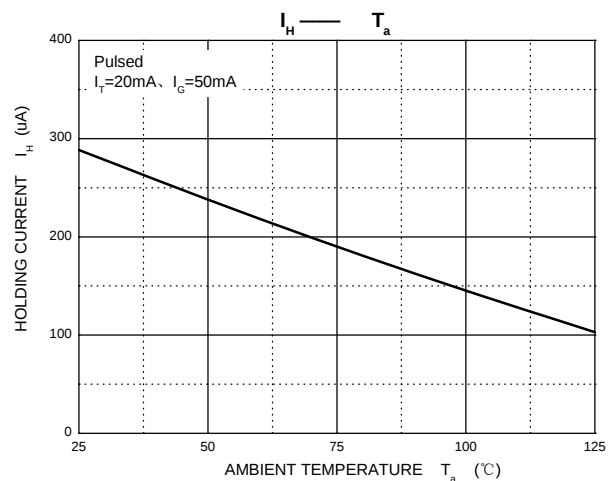
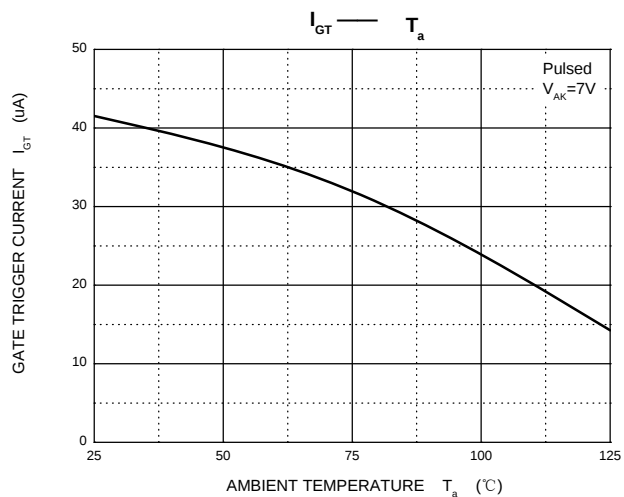
ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol		Test conditions	Min	Max	Unit
On state voltage	V_{TM}^*		$I_{TM}=1A$		1.7	V
Gate trigger voltage	V_{GT}		$V_{AK}=7V$		0.8	V
Peak Repetitive forward and reverse blocking voltage MCR100-6 MCR100-8	V_{DRM} AND V_{RRM}		$I_{DRM}=10\mu A$	400 600		V
Peak forward or reverse blocking Current	I_{DRM} I_{RRM}		$V_{AK}=\text{Rated}$ V_{DRM} OR V_{RRM}		10	μA
Holding current	I_H		$I_{HL}=20mA, V_{AK}=7V$		5	mA
Gate trigger current	I_{GT}	A2	$V_{AK}=7V$	5	15	μA
		A1		15	30	μA
		A		30	80	μA
		B		80	200	μA

* Forward current applied for 1 ms maximum duration, duty cycle $\leq 1\%$.

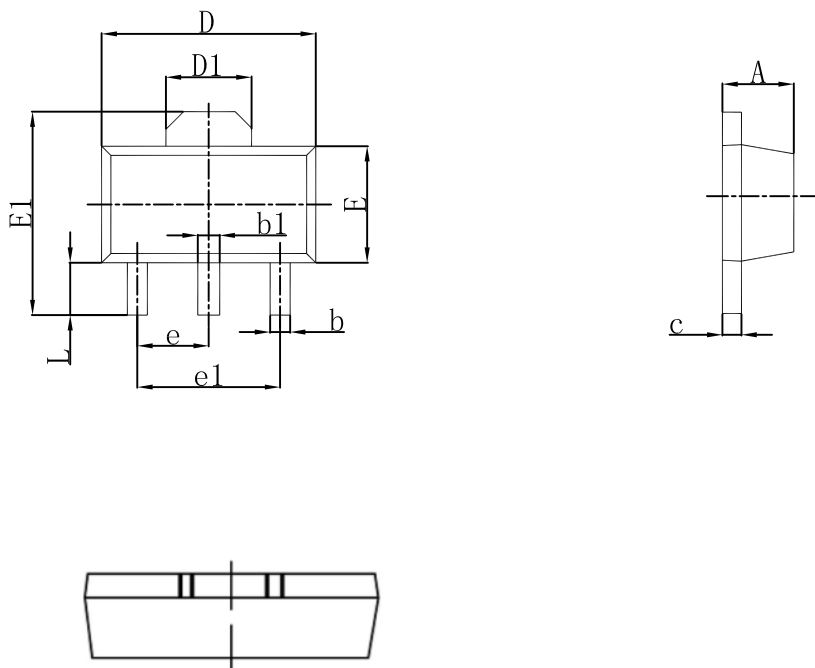


Typical Characteristics





SOT-89-3L Outlines Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.400	1.600	0.055	0.063
b	0.320	0.520	0.013	0.020
b1	0.400	0.580	0.016	0.023
c	0.350	0.440	0.014	0.017
D	4.400	4.600	0.173	0.181
D1	1.550 REF.		0.061 REF.	
E	2.300	2.600	0.091	0.102
E1	3.940	4.250	0.155	0.167
e	1.500 TYP.		0.060 TYP.	
e1	3.000 TYP.		0.118 TYP.	
L	0.900	1.200	0.035	0.047